

High-performance polishing slurry for SiC wafers

NANOBITM

Application

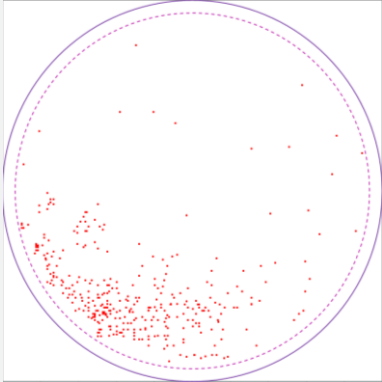
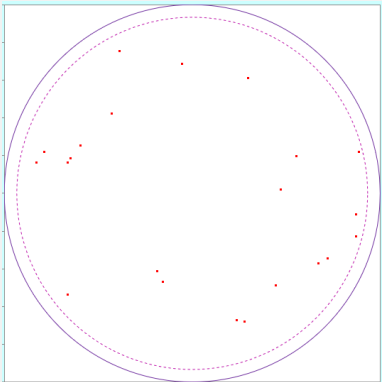
- Polishing slurry mixed of two components for SiC wafers.

Summary

- High-speed, low-damage processing in a single step with MnO₂ abrasives
- Stable processing enabled by minimizing the rate difference between C-face and Si-face
- Easy equipment and water cleaning
- Reusable in a circulation system



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	Commercially available epi-ready wafer	After polishing with NANOBI TM
Mapping of sub surface damage detected		
Density of sub surface damage	158(/cm ²)	10(/cm ²)

※ Evaluation using a mirror electron microscope(Mirelis VM1000 by Hitachi High-Tech Co.)